



60A08

Sensitive Gate Triacs

HAOPIN MICROELECTRONICS CO.,LTD.

Description

Passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants.

Symbol	Simplified outline
	 TO-92
Pin	Description
1	Main terminal 1 (T1)
2	gate (G)
3	Main terminal 2 (T2)

Applications:

- ◆ Motor control
- ◆ Industrial and domestic lighting
- ◆ Heating
- ◆ Static switching

Features

- ◆ Blocking voltage to 600 V
- ◆ On-state RMS current to 0.8 A

SYMBOL	PARAMETER	Value	Unit
V_{DRM}	Repetitive peak off-state voltages	600	V
$I_T \text{ (RMS)}$	RMS on-state current (full sine wave)	0.8	A
I_{TSM}	Non-repetitive peak on-state current	9	A

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	Value	UNIT
$R_{th(j-l)}$	Junction to lead (AC)	-	-	-	60	°C/W
$R_{th j-a}$	Junction to ambient	-		-	150	°C/W



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Limiting values in accordance with the Maximum system(IEC 134)

SYMBOL	PARAMETER	CONDITIONS			MIN	Value	UNIT
V_{DSM}/V_{RSM}					-	-	V
$I_{T(RMS)}$	RMS on-state current	Full sine wave; $T_j=50^\circ C$			-	0.8	A
I_{TSM}	Non repetitive surge peak on-state current	full cycle, T_j initial= $25^\circ C$	$f=50$ Hz $f=60$ Hz	$t=20ms$ $t=16.7ms$	-	9	A
					-	9.5	A
I^2t	I^2t Value for fusing	$T_p=10ms$			-	0.45	A^2s
DI/dt	Critical rate of rise of on-state current	$I_G=2x I_{GT, tr} \leq 100ns$	$f=120Hz$	$T_j=110^\circ C$	-	20	$A/\mu s$
I_{GM}	Peak gate current	$t_p=20\mu s$			$T_j=110^\circ C$	-	A
I_{DRM}	$V_{DRM}=V_{RRM}=600V$				$T_j=25^\circ C$	-	μA
I_{RRM}	$V_{DRM}=V_{RRM}=600V$				$T_j=110^\circ C$	-	mA
$P_{G(AV)}$	Average gate power				$T_j=110^\circ C$	-	W
T_{stg}	Storage temperature range				-40	150	$^\circ C$
T_j	Operating junction Temperature range				-40	110	$^\circ C$

 $T_j=25^\circ C$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Static characteristics						
I_{GT1} V_{GT}		$V_D=12V$; $RL=33\Omega$	I-II-III IV ALL	-	-	5 7 1.3 mA mA V
I_L		$I_G=1.2 I_{GT}$	I-III-IV II	-	-	10 20 mA mA
I_{H2} V_{GD}		$I_L=200mA$ $V_D=V_{DRM}$ $R_L=3.3K\Omega$ $T_j=110^\circ C$ ALL	-	-	-	5 mA V
dV/dt2		$V_D=67\% V_{DRM}$ gate open; $T_j=110^\circ C$	10	-	-	V/us
(Dv/dt)c(2)		(Di/dt)c=0.35A/ms; $T_j=110^\circ C$	1.5	-	-	V/us

Dynamic Characteristics

$V_{TM}(2)$	$I_{TM}=1.1A$ $t_p=380\mu s$	$T_j=25^\circ C$			1.5	V
V_{to} R_d	Threshold voltage Dynamic resistance	$T_j=110^\circ C$ $T_j=110^\circ C$			0.95 420 mΩ	V mΩ

Description

Fig 1: Maximum power dissipation versus RMS on-state current.

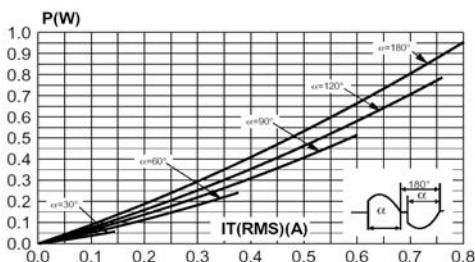


Fig 2: Correlation between maximum power dissipation and maximum allowable temperatures (Tamb and Tlead).

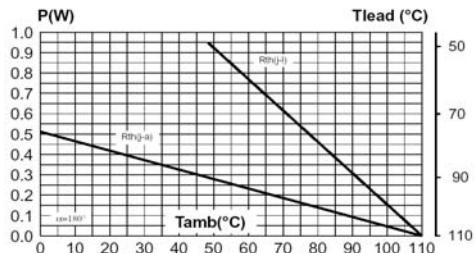


Fig 3: RMS on-state current versus ambient temperature.

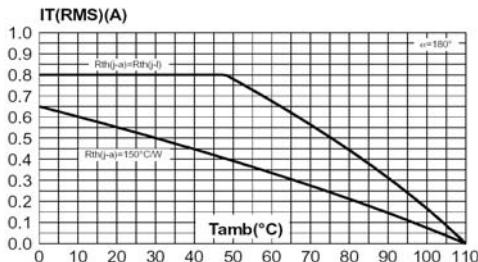


Fig 4: Relative variation of thermal impedance junction to ambient versus pulse duration.

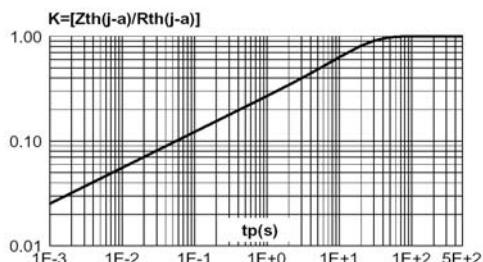


Fig 5: Relative variation of gate trigger current and holding current versus junction temperature (typical values).

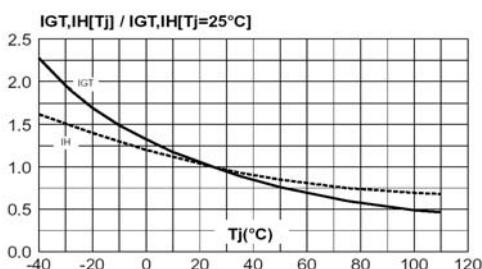
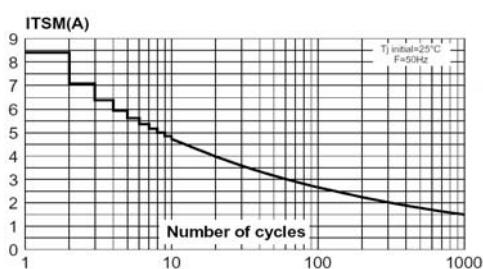


Fig 6: Non repetitive surge peak on-state current versus number of cycles.





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Fig 7: Non repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t .

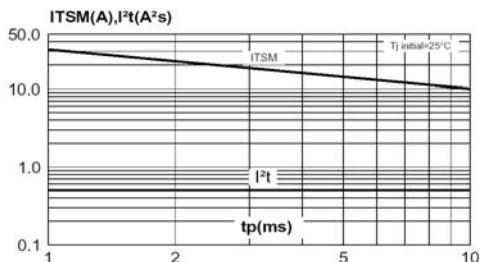
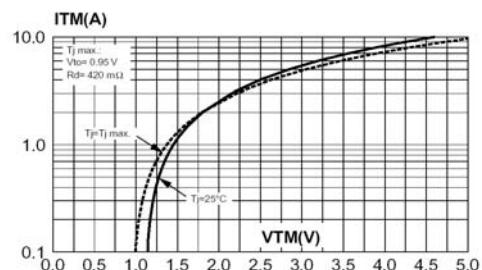


Fig 8: On-state characteristics (maximum values).





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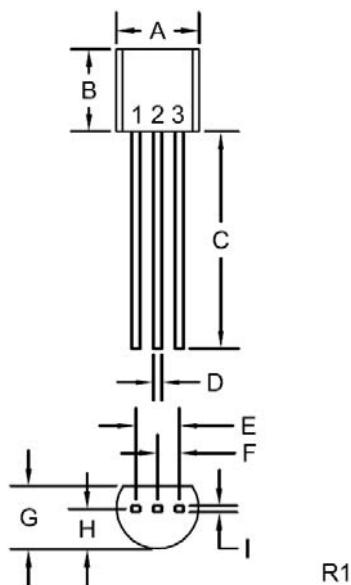
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MECHANICAL DATA

Dimensions in mm

Net Mass: 0.2 g

TO-92



SYMBOL	DIMENSIONS			
	INCHES	MILLIMETERS	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100	-	2.54	-
F	0.050	-	1.27	-
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015	-	0.38	-

TO-92 (REV: R1)